Silicon PNP Power Transistors 2SA636 2SA636A

DESCRIPTION

- With TO-202 package
- Complement to type 2SC1098/1098A
- High breakdown voltage
- High transition frequency

APPLICATIONS

- For audio frequency power amplifier and low speed switching applications

PINNING(see Fig.2)

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

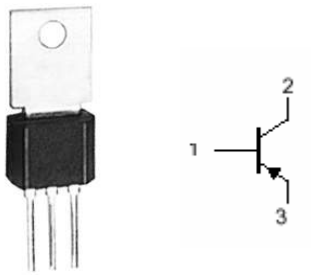

Fig.1 simplified outline (TO-202) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER		CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage		Open emitter	-70	V
V_{CEO}	Collector-emitter voltage	2SA636	Open base	-45	V
		2SA636A		-60	
V_{EBO}	Emitter-base voltage		Open collector	-5	V
I_C	Collector current			-3	A
I_{CM}	Collector current-peak			-5	A
I_B	Base current			-0.6	A
P_T	Total power dissipation		T_C=25℃	10	W
			T_a=25℃	1.2	
T_j	Junction temperature			150	℃
T_{stg}	Storage temperature			-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V_{CEsat}	Collector-emitter saturation voltage	I_C=-1.5A ;I_B=-0.15A		-0.5	-2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-1.5A ;I_B=-0.15A		-0.8	-2.0	V
I_{CBO}	Collector cut-off current	V_{CB}=-45V; I_E=0			-1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-3V; I_C=0			-1	μA
h_{FE-1}	DC current gain	I_C=-20mA ; V_{CE}=-5V	20			
h_{FE-2}	DC current gain	I_C=-0.5A ; V_{CE}=-5V	40		250	
C_{OB}	Output capacitance	I_E=0; V_{CB}=-10V;f=1MHz		60		pF
f_T	Transition frequency	I_C=-0.1A ; V_{CB}=-5V		45		MHz

◆ **h_{FE-2} classifications**

N	M	L	K
40-60	50-100	80-160	120-250

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PACKAGE OUTLINE

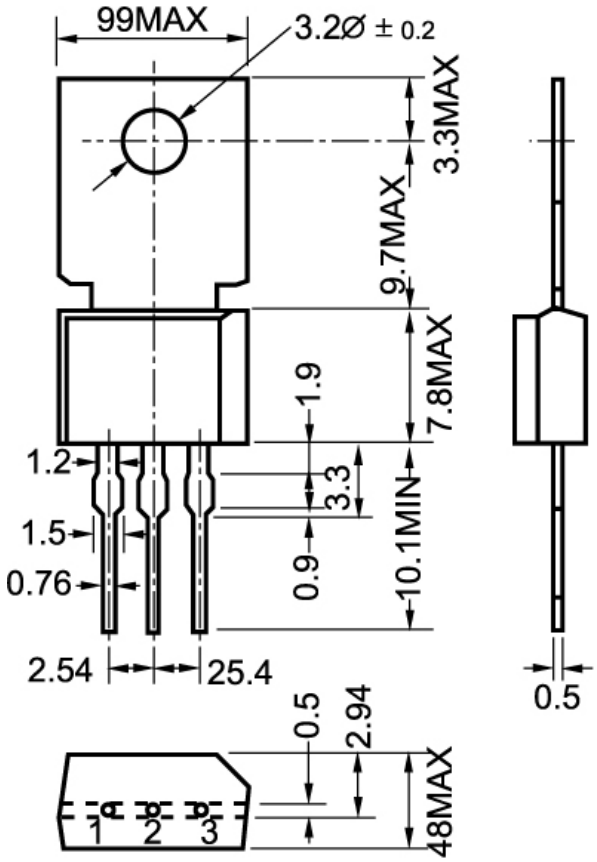

Fig.2 outline dimensions